

U.S. National Phase of PCT/JP2004/013633

Filed : Herewith

AMENDMENTS TO THE SPECIFICATION

At page 1, please delete the section entitled "TECHNICAL FIELD" (lines 6-11), and replace with the following:

CROSS-REFERENCE TO RELATED APPLICATIONS

This application is the U.S. National Phase filing under 35 U.S.C. §371 of PCT/JP2004/012235, filed August 19, 2004, which designated the United States and was published in English, which Priority is claimed on claims priority to Japanese Patent Application No. 2003-325953, filed September 18, 2003, the entire content contents of which is are incorporated herein by reference.

TECHNICAL FIELD

The present invention relates to a positive photoresist composition and to a resist pattern formation method.